



SANYO Semiconductors

DATA SHEET

CPH6332 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- High-speed switching.
- 1.8V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-6	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-24	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm²×0.8mm)	1.6	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0V	-20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _D =-20V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _D =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _D =-10V, I _D =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	y _{fs}	V _D =-10V, I _D =-3A	5.8	9.6		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-3A, V _{GS} =-4V		27	36	mΩ
	R _{DS(on)2}	I _D =-1.5A, V _{GS} =-2.5V		36	51	mΩ
	R _{DS(on)3}	I _D =-0.6A, V _{GS} =-1.8V		58	88	mΩ

Marking : YJ

Continued on next page.

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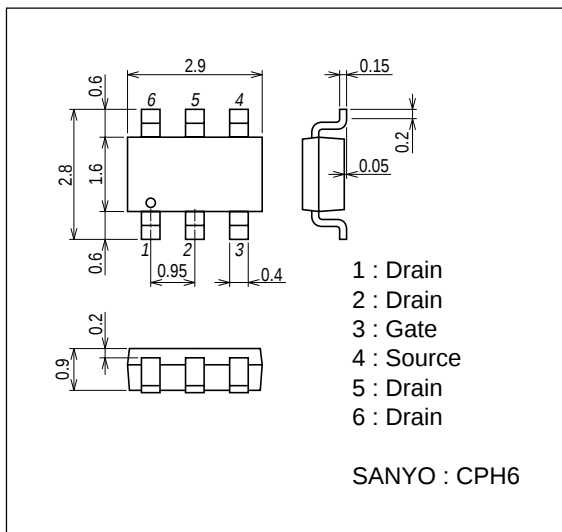
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	C_{iss}	$V_{DS}=-10V, f=1MHz$		1500		pF
Output Capacitance	C_{oss}	$V_{DS}=-10V, f=1MHz$		230		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=-10V, f=1MHz$		180		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		17		ns
Rise Time	t_r	See specified Test Circuit.		135		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		110		ns
Fall Time	t_f	See specified Test Circuit.		140		ns
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-4V, I_D=-6A$		12		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=-10V, V_{GS}=-4V, I_D=-6A$		2.7		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=-10V, V_{GS}=-4V, I_D=-6A$		3.7		nC
Diode Forward Voltage	V_{SD}	$I_S=-6A, V_{GS}=0V$		-0.82	-1.5	V

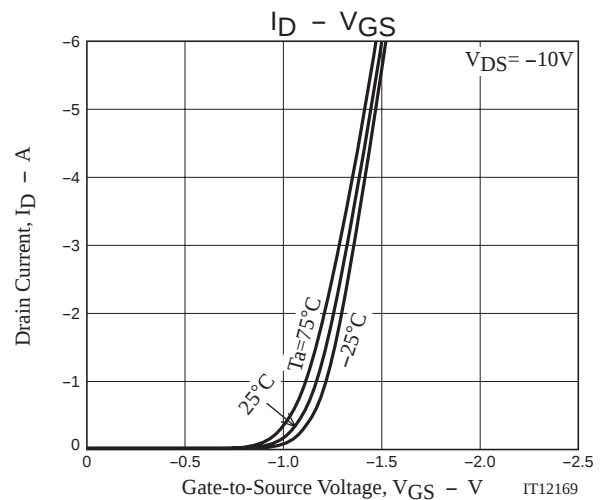
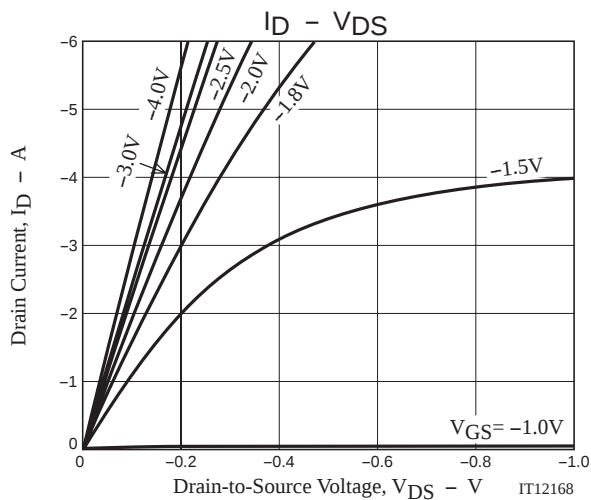
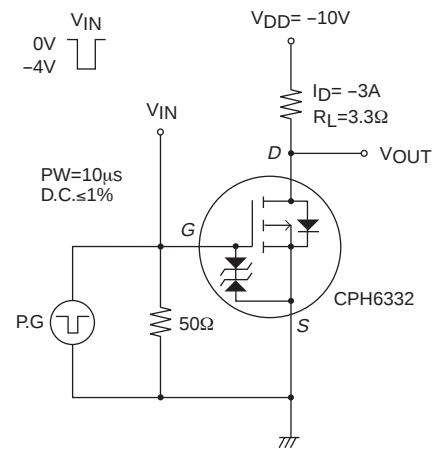
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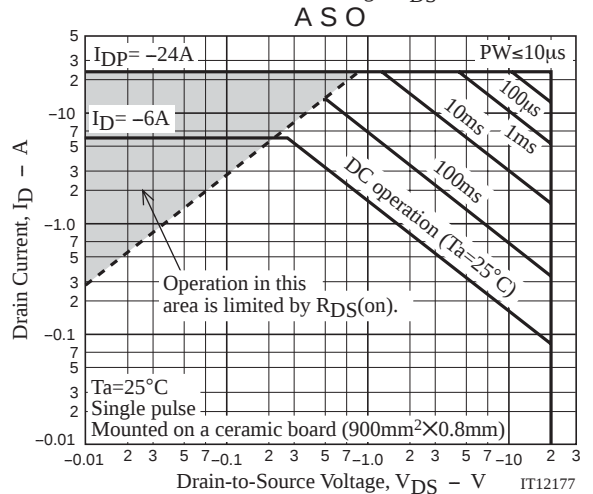
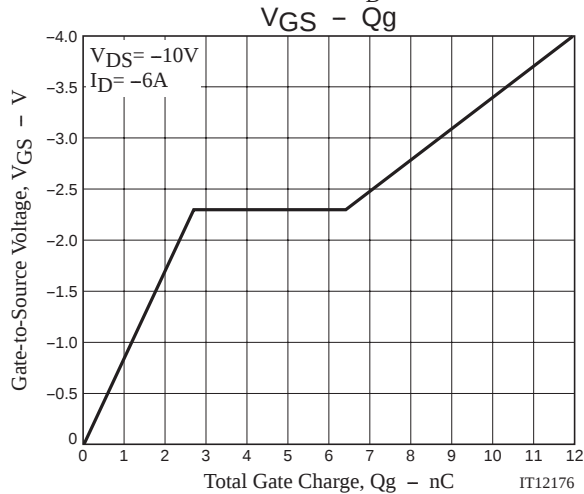
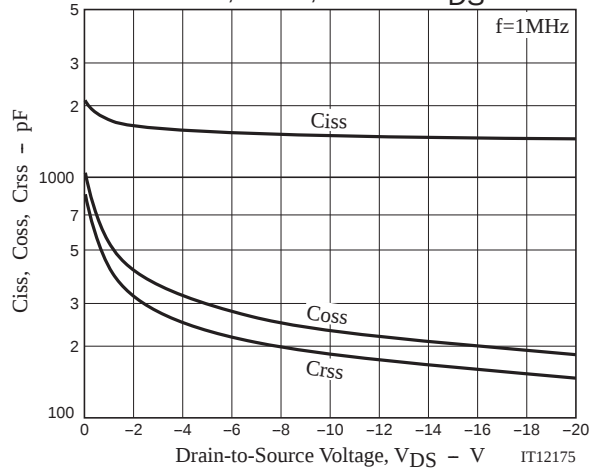
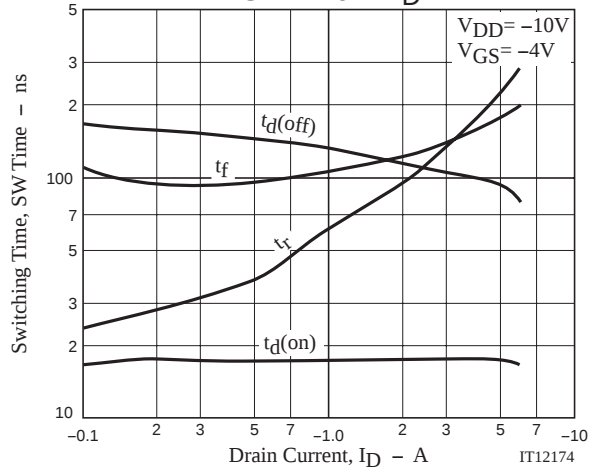
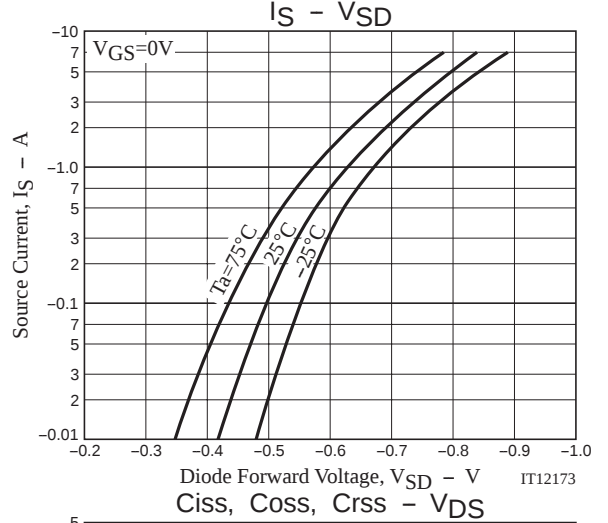
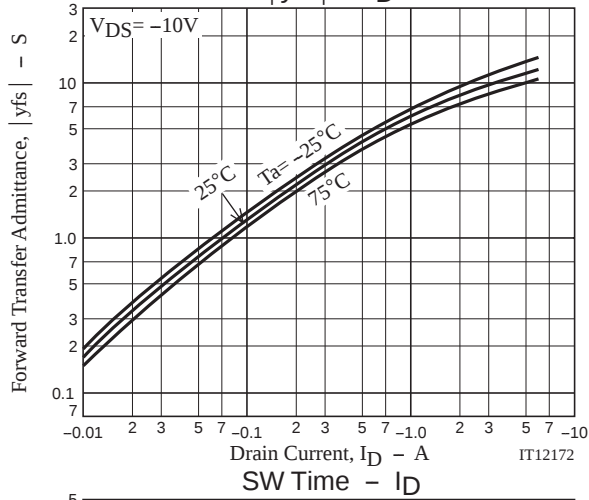
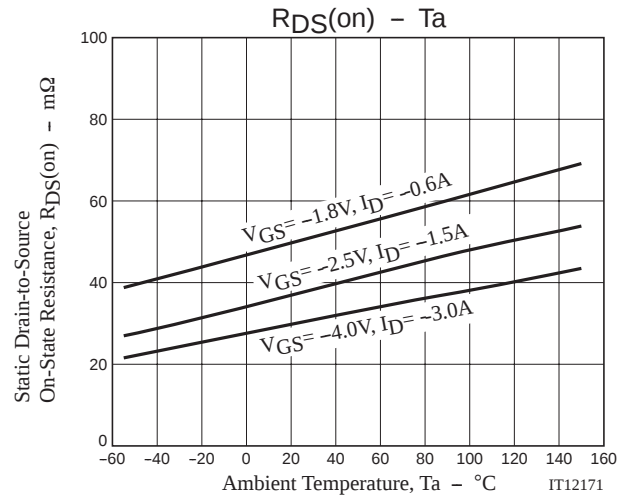
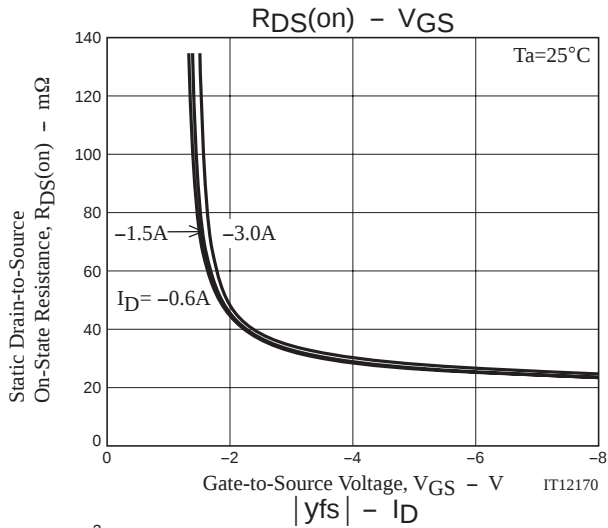
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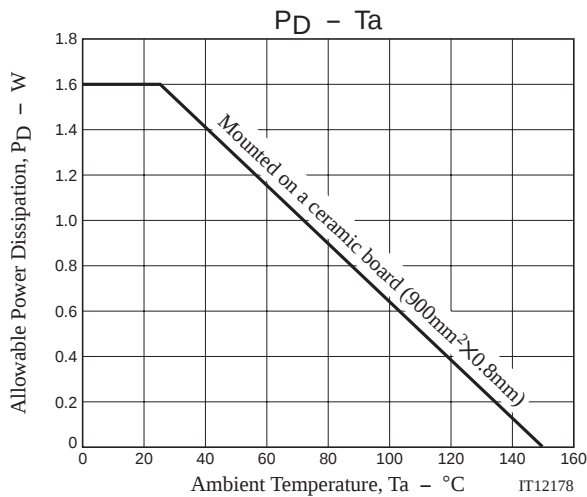
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Switching Time Test Circuit







Note on usage : Since the CPH6332 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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